



**16-Mbit (1 M words × 16 bit) Static RAM with Error-Correcting Code (ECC)**

**Features**

- High speed
  - $t_{AA} = 10 \text{ ns}/15 \text{ ns}$
- Embedded error-correcting code (ECC) for single-bit error correction
- Low active and standby currents
  - $I_{CC} = 90\text{-mA}$  typical at 100 MHz
  - $I_{SB2} = 20\text{-mA}$  typical
- Operating voltage range: 1.65 V to 2.2 V, 2.2 V to 3.6 V, and 4.5 V to 5.5 V
- 1.0-V data retention
- Transistor-transistor logic (TTL) compatible inputs and outputs
- Error indication (ERR) pin to indicate 1-bit error detection and correction
- Available in Pb-free 48-pin TSOP I, 54-pin TSOP II, and 48-ball VFBGA packages

**Functional Description**

CY7C1061G and CY7C1061GE are high-performance CMOS fast static RAM devices with embedded ECC<sup>[1]</sup>. Both devices are offered in single and dual chip enable options and in multiple pin configurations. The CY7C1061GE device includes an ERR pin that signals a single-bit error-detection and correction event during a read cycle.

To access devices with a single chip enable input, assert the chip enable (CE) input LOW. To access dual chip enable devices, assert both chip enable inputs – CE<sub>1</sub> as LOW and CE<sub>2</sub> as HIGH.

To perform data writes, assert the Write Enable ( $\overline{WE}$ ) input LOW, and provide the data and address on the device data pins (I/O<sub>0</sub> through I/O<sub>15</sub>) and address pins (A<sub>0</sub> through A<sub>19</sub>) respectively. The Byte High Enable (BHE) and Byte Low Enable (BLE) inputs control byte writes, and write data on the corresponding I/O lines to the memory location specified. BHE controls I/O<sub>8</sub> through I/O<sub>15</sub> and BLE controls I/O<sub>0</sub> through I/O<sub>7</sub>.

To perform data reads, assert the Output Enable ( $\overline{OE}$ ) input and provide the required address on the address lines. Read data is accessible on I/O lines (I/O<sub>0</sub> through I/O<sub>15</sub>). You can perform byte accesses by asserting the required byte enable signal (BHE or BLE) to read either the upper byte or the lower byte of data from the specified address location.

All I/Os (I/O<sub>0</sub> through I/O<sub>15</sub>) are placed in a high-impedance state when the device is deselected (CE HIGH for a single chip enable device and CE<sub>1</sub> HIGH / CE<sub>2</sub> LOW for a dual chip enable device), or control signals are de-asserted ( $\overline{OE}$ , BLE, BHE).

On the CY7C1061GE devices, the detection and correction of a single-bit error in the accessed location is indicated by the assertion of the ERR output (ERR = High). See the [Truth Table on page 16](#) for a complete description of read and write modes.

The logic block diagrams are on page 2.

The CY7C1061G and CY7C1061GE devices are available in 48-pin TSOP I, 54-pin TSOP II, and 48-ball VFBGA packages.

For a complete list of related documentation, click [here](#).

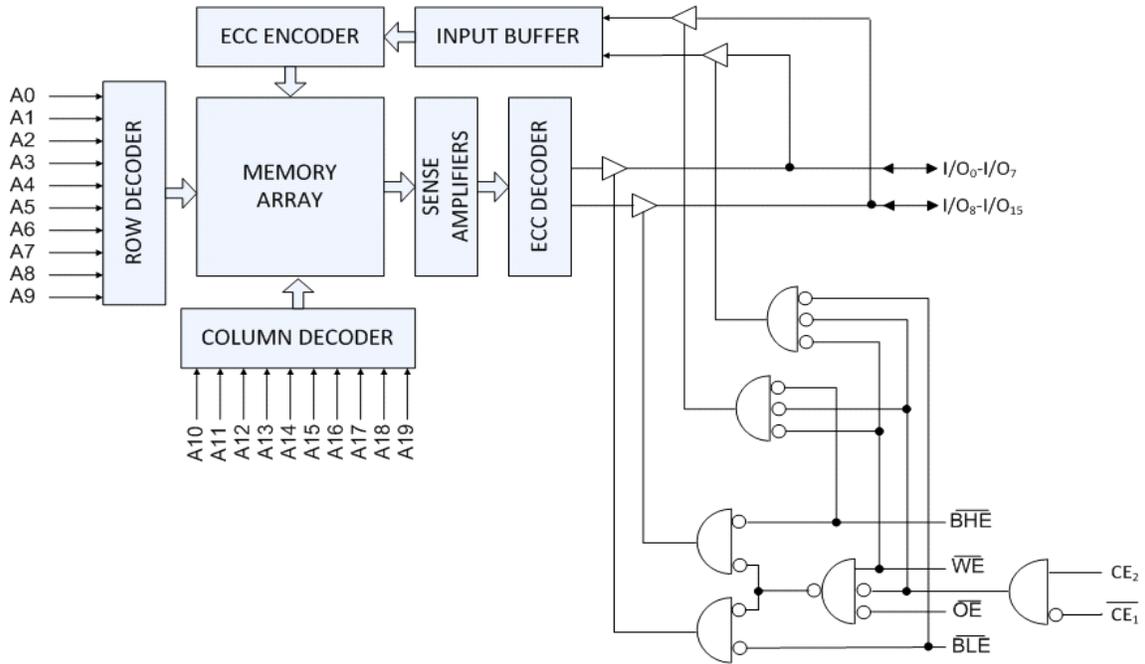
**Product Portfolio**

Product	Features and Options (see “Pin Configurations” on page 4)	Range	V <sub>CC</sub> Range (V)	Speed (ns) 10/15	Current Consumption			
					Operating I <sub>CC</sub> , (mA)		Standby, I <sub>SB2</sub> (mA)	
					f = f <sub>max</sub>			
					Typ <sup>[2]</sup>	Max	Typ <sup>[2]</sup>	Max
CY7C1061G18	Single or dual chip enables	Industrial	1.65 V–2.2 V	15	70	80	20	30
CY7C1061G(E)30			2.2 V–3.6 V	10	90	110		
CY7C1061G	Optional ERR pins  Address MSB A <sub>19</sub> pin placement options compatible with Cypress and other vendors		4.5 V–5.5 V	10	90	110		

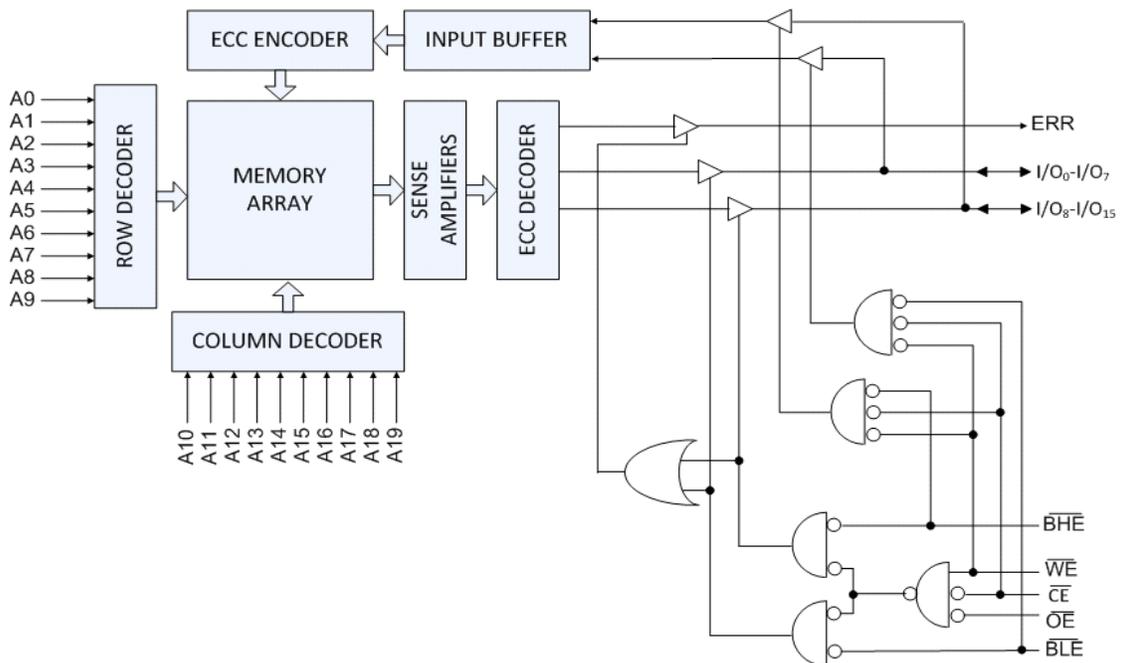
**Notes**

1. This device does not support automatic write-back on error detection.
2. Typical values are included only for reference and are not guaranteed or tested. Typical values are measured at V<sub>CC</sub> = 1.8 V (for a V<sub>CC</sub> range of 1.65 V–2.2 V), V<sub>CC</sub> = 3 V (for a V<sub>CC</sub> range of 2.2 V–3.6 V), and V<sub>CC</sub> = 5 V (for a V<sub>CC</sub> range of 4.5 V–5.5 V), T<sub>A</sub> = 25 °C.

Logic Block Diagram – CY7C1061G



Logic Block Diagram – CY7C1061GE



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### Pin Configurations

Figure 1. 48-ball VFBGA (6 × 8 × 1.0 mm)

Dual Chip Enable without ERR, Address MSB A19 at Ball G2, CY7C1061G<sup>[3]</sup> Package/Grade ID: BVJXI

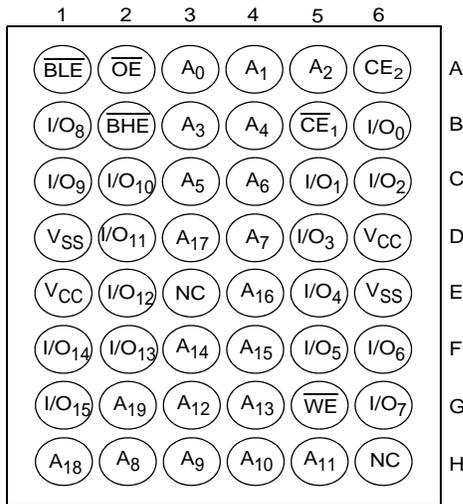


Figure 2. 48-ball VFBGA (6 × 8 × 1.0 mm)

Dual Chip Enable without ERR, Address MSB A19 at Ball H6, CY7C1061G<sup>[3]</sup> Package/Grade ID: BVXI

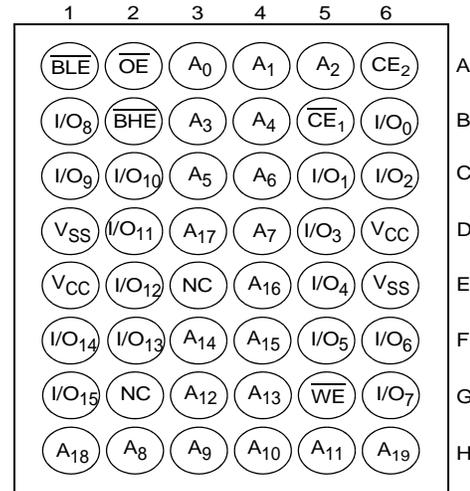
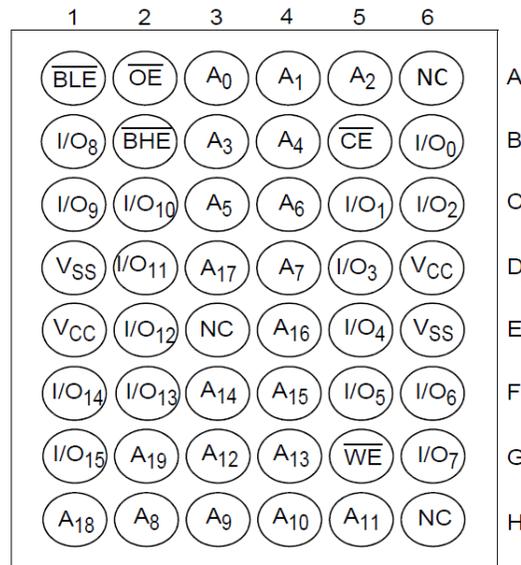


Figure 3. 48-ball VFBGA (6 × 8 × 1.0 mm) Single Chip Enable without ERR, Address MSB A19 at Ball G2, CY7C1061G<sup>[3]</sup> Package/Grade ID: BV1XI



**Note**

3. NC pins are not connected internally to the die.

Pin Configurations (continued)

Figure 4. 48-ball VFBGA (6 × 8 × 1.0 mm)  
Single Chip Enable with ERR, Address MSB A19 at Ball G2  
CY7C1061GE<sup>[4, 5]</sup> Package/Grade ID: BV1XI

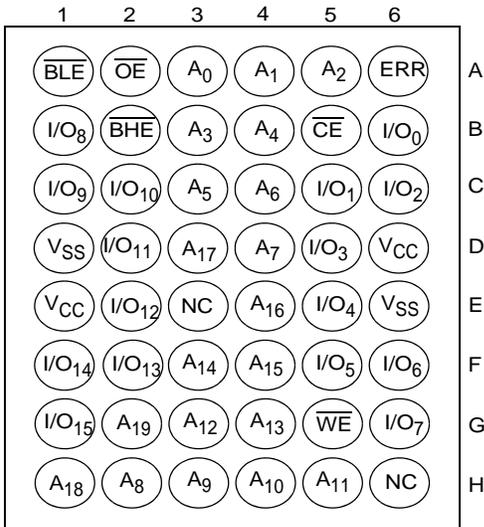


Figure 5. 48-ball VFBGA (6 × 8 × 1.0 mm)  
Dual Chip Enable with ERR, Address MSB A19 at Ball G2  
CY7C1061GE<sup>[4, 5]</sup> Package/Grade ID: BVJXI

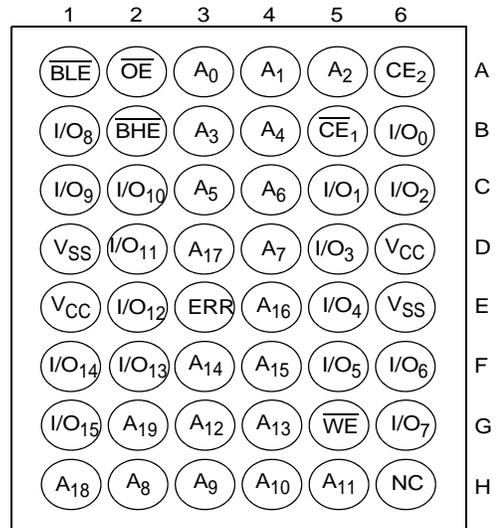
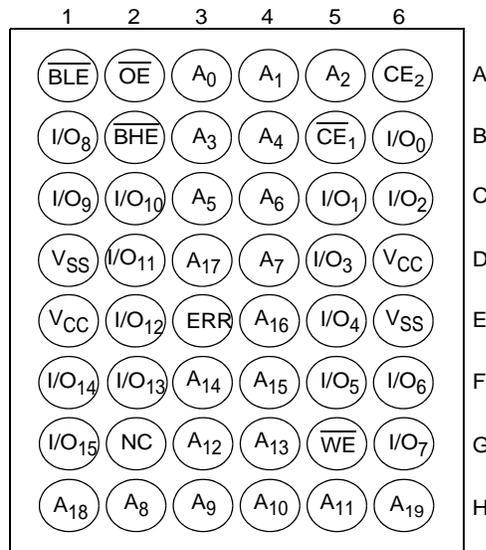


Figure 6. 48-ball VFBGA (6 × 8 × 1.0 mm) Dual Chip Enable with ERR, Address MSB A19 at Ball H6  
CY7C1061GE<sup>[4, 5]</sup> Package/Grade ID: BVXI



Notes

- 4. NC pins are not connected internally to the die.
- 5. ERR is an Output pin. If not used, this pin should be left floating.

Pin Configurations (continued)

Figure 7. 48-pin TSOP I (12 × 18.4 × 1 mm)  
Single Chip Enable with ERR  
CY7C1061GE<sup>[6, 7]</sup> Package/Grade ID: ZXI

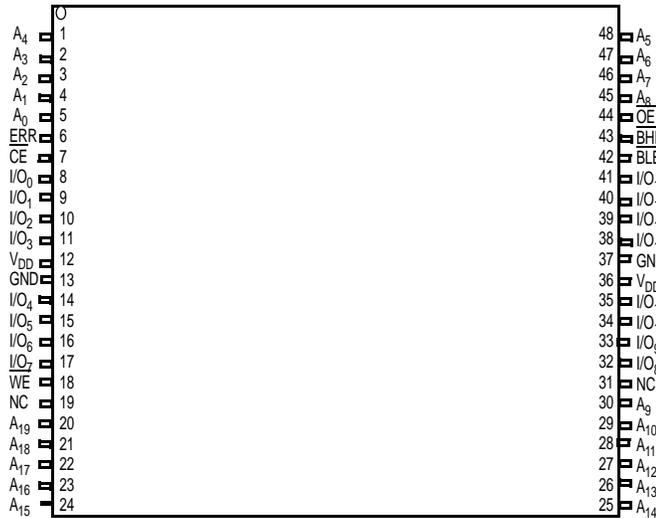


Figure 8. 48-pin TSOP I (12 × 18.4 × 1 mm)  
Single Chip Enable without ERR  
CY7C1061G<sup>[6]</sup> Package/Grade ID: ZXI

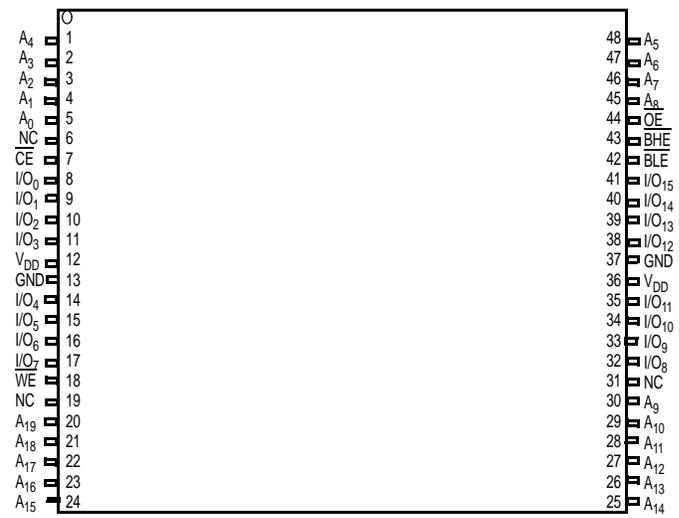


Figure 9. 54-pin TSOP II (22.4 × 11.84 × 1.0 mm)  
Dual Chip Enable without ERR  
CY7C1061G<sup>[6]</sup> Package/Grade ID: ZSXI

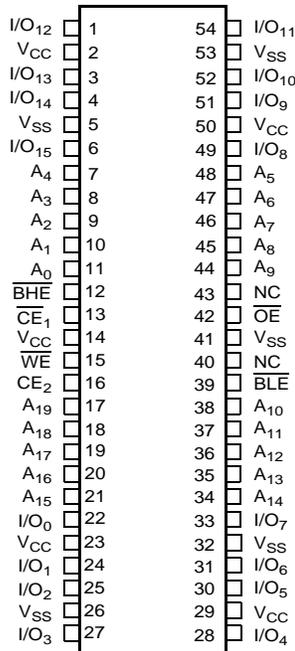
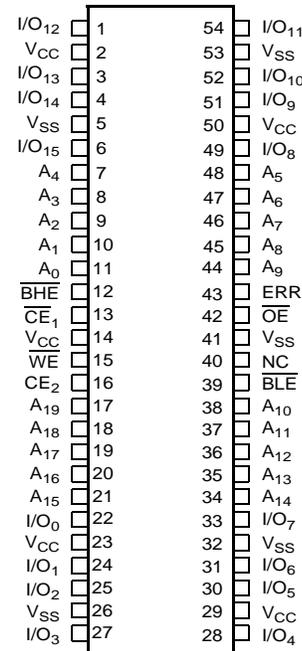


Figure 10. 54-pin TSOP II (22.4 × 11.84 × 1.0 mm)  
Dual Chip Enable with ERR  
CY7C1061GE<sup>[6, 7]</sup> Package/Grade ID: ZSXI



Notes

- 6. NC pins are not connected internally to the die.
- 7. ERR is an Output pin. If not used, this pin should be left floating.

## Maximum Ratings

Exceeding maximum ratings may impair the useful life of the device. These user guidelines are not tested.

Storage temperature ..... -65 °C to +150 °C

Ambient temperature with power applied ..... -55 °C to +125 °C

Supply voltage on  $V_{CC}$  relative to GND ..... -0.5 V to  $V_{CC} + 0.5$  V

DC voltage applied to outputs in High Z State <sup>[8]</sup> ..... -0.5 V to  $V_{CC} + 0.5$  V

DC input voltage<sup>[8]</sup> ..... -0.5 V to  $V_{CC} + 0.5$  V

Current into outputs (LOW) ..... 20 mA

Static discharge voltage (MIL-STD-883, Method 3015) ..... > 2001 V

Latch-up current ..... > 140 mA

## Operating Range

Grade	Ambient Temperature	$V_{CC}$
Industrial	-40 °C to +85 °C	1.65 V to 2.2 V, 2.2 V to 3.6 V, 4.5 V to 5.5 V

## DC Electrical Characteristics

Over the operating range of -40 °C to 85 °C

Parameter	Description	Test Conditions	10 ns / 15 ns			Unit	
			Min	Typ <sup>[10]</sup>	Max		
$V_{OH}$	Output HIGH voltage	1.65 V to 2.2 V $V_{CC} = \text{Min}, I_{OH} = -0.1$ mA	1.4	-	-	V	
		2.2 V to 2.7 V $V_{CC} = \text{Min}, I_{OH} = -1.0$ mA	2.0	-	-		
		2.7 V to 3.6 V $V_{CC} = \text{Min}, I_{OH} = -4.0$ mA	2.2	-	-		
		4.5 V to 5.5 V $V_{CC} = \text{Min}, I_{OH} = -4.0$ mA	2.4	-	-		
		4.5 V to 5.5 V $V_{CC} = \text{Min}, I_{OH} = -0.1$ mA	$V_{CC} - 0.4$ <sup>[11]</sup>	-	-		
$V_{OL}$	Output LOW voltage	1.65 V to 2.2 V $V_{CC} = \text{Min}, I_{OL} = 0.1$ mA	-	-	0.2	V	
		2.2 V to 2.7 V $V_{CC} = \text{Min}, I_{OL} = 2$ mA	-	-	0.4		
		2.7 V to 3.6 V $V_{CC} = \text{Min}, I_{OL} = 8$ mA	-	-	0.4		
		4.5 V to 5.5 V $V_{CC} = \text{Min}, I_{OL} = 8$ mA	-	-	0.4		
$V_{IH}$ <sup>[8]</sup>	Input HIGH voltage	1.65 V to 2.2 V	1.4	-	$V_{CC} + 0.2$	V	
		2.2 V to 2.7 V	2.0	-	$V_{CC} + 0.3$		
		2.7 V to 3.6 V	2.0	-	$V_{CC} + 0.3$		
		4.5 V to 5.5 V	2.2	-	$V_{CC} + 0.5$		
$V_{IL}$ <sup>[8]</sup>	Input LOW voltage	1.65 V to 2.2 V	-0.2	-	0.4	V	
		2.2 V to 2.7 V	-0.3	-	0.6		
		2.7 V to 3.6 V	-0.3	-	0.8		
		4.5 V to 5.5 V	-0.5	-	0.8		
$I_{IX}$	Input leakage current	$GND \leq V_{IN} \leq V_{CC}$	-1.0	-	+1.0	$\mu$ A	
$I_{OZ}$	Output leakage current	$GND \leq V_{OUT} \leq V_{CC}$ , Output disabled	-1.0	-	+1.0	$\mu$ A	
$I_{CC}$	Operating supply current	$V_{CC} = \text{Max}, I_{OUT} = 0$ mA, CMOS levels	f = 100 MHz	-	90.0	110.0	mA
			f = 66.7 MHz	-	70.0	80.0	
$I_{SB1}$	Automatic CE power down current – TTL inputs	Max $V_{CC}$ , $\overline{CE} \geq V_{IH}$ <sup>[9]</sup> , $V_{IN} \geq V_{IH}$ or $V_{IN} \leq V_{IL}$ , f = f <sub>MAX</sub>	-	-	40.0	mA	
$I_{SB2}$	Automatic CE power down current – CMOS inputs	Max $V_{CC}$ , $\overline{CE} \geq V_{CC} - 0.2$ V <sup>[9]</sup> , $V_{IN} \geq V_{CC} - 0.2$ V or $V_{IN} \leq 0.2$ V, f = 0	-	20.0	30.0	mA	

### Notes

8.  $V_{IL(\text{min})} = -2.0$  V and  $V_{IH(\text{max})} = V_{CC} + 2$  V for pulse durations of less than 2 ns.

9. For all dual chip enable devices,  $\overline{CE}$  is the logical combination of  $\overline{CE}_1$  and  $CE_2$ . When  $\overline{CE}_1$  is LOW and  $CE_2$  is HIGH,  $\overline{CE}$  is LOW; when  $\overline{CE}_1$  is HIGH or  $CE_2$  is LOW,  $\overline{CE}$  is HIGH.

10. Typical values are included only for reference and are not guaranteed or tested. Typical values are measured at  $V_{CC} = 1.8$  V (for a  $V_{CC}$  range of 1.65 V–2.2 V),  $V_{CC} = 3$  V (for a  $V_{CC}$  range of 2.2 V–3.6 V), and  $V_{CC} = 5$  V (for a  $V_{CC}$  range of 4.5 V–5.5 V),  $T_A = 25$  °C.

11. This parameter is guaranteed by design and is not tested

### Capacitance

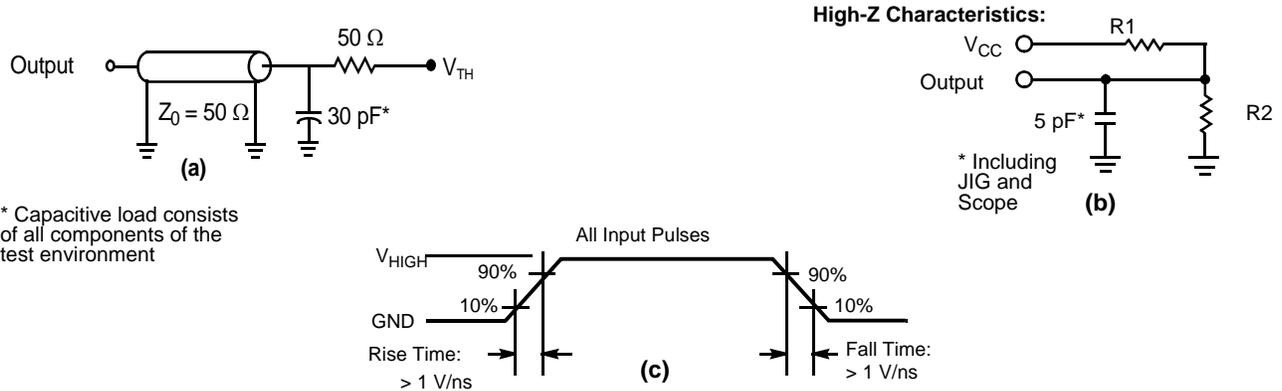
Parameter <sup>[12]</sup>	Description	Test Conditions	54-pin TSOP II	48-ball VFBGA	48-pin TSOP I	Unit
C <sub>IN</sub>	Input capacitance	T <sub>A</sub> = 25 °C, f = 1 MHz, V <sub>CC</sub> = V <sub>CC(typ)</sub>	10	10	10	pF
C <sub>OUT</sub>	I/O capacitance		10	10	10	pF

### Thermal Resistance

Parameter <sup>[12]</sup>	Description	Test Conditions	54-pin TSOP II	48-ball VFBGA	48-pin TSOP I	Unit
θ <sub>JA</sub>	Thermal resistance (junction to ambient)	Still air, soldered on a 3 × 4.5 inch, four layer printed circuit board	93.63	31.50	57.99	°C/W
θ <sub>JC</sub>	Thermal resistance (junction to case)		21.58	15.75	13.42	°C/W

### AC Test Loads and Waveforms

Figure 11. AC Test Loads and Waveforms<sup>[13]</sup>



\* Capacitive load consists of all components of the test environment

Parameters	1.8 V	3.0 V	5.0 V	Unit
R1	1667	317	317	Ω
R2	1538	351	351	Ω
V <sub>TH</sub>	0.9	1.5	1.5	V
V <sub>HIGH</sub>	1.8	3	3	V

#### Notes

12. Tested initially and after any design or process changes that may affect these parameters.

13. Full-device AC operation assumes a 100-μs ramp time from 0 to V<sub>CC</sub> (min) and 100-μs wait time after V<sub>CC</sub> stabilizes to its operational value.

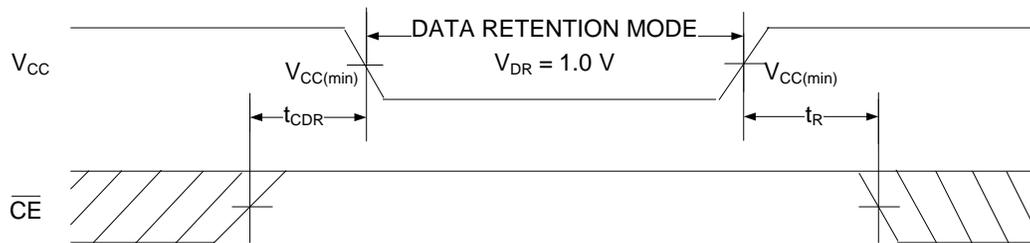
### Data Retention Characteristics

Over the operating range of -40 °C to 85 °C

Parameter	Description	Conditions	Min	Max	Unit
$V_{DR}$	$V_{CC}$ for data retention		1.0	-	V
$I_{CCDR}$	Data retention current	$V_{CC} = V_{DR}, \overline{CE} \geq V_{CC} - 0.2 \text{ V}^{[14]}, V_{IN} \geq V_{CC} - 0.2 \text{ V}$ or $V_{IN} \leq 0.2 \text{ V}$	-	30.0	mA
$t_{CDR}^{[15]}$	Chip deselect to data retention time		0	-	ns
$t_R^{[15, 16]}$	Operation recovery time	$V_{CC} \geq 2.2 \text{ V}$	10.0	-	ns
		$V_{CC} < 2.2 \text{ V}$	15.0	-	ns

### Data Retention Waveform

Figure 12. Data Retention Waveform <sup>[14]</sup>



**Notes**

- 14. For all dual chip enable devices,  $\overline{CE}$  is the logical combination of  $\overline{CE}_1$  and  $CE_2$ . When  $\overline{CE}_1$  is LOW and  $CE_2$  is HIGH,  $\overline{CE}$  is LOW; when  $\overline{CE}_1$  is HIGH or  $CE_2$  is LOW,  $\overline{CE}$  is HIGH.
- 15. This parameter is guaranteed by design and is not tested
- 16. Full-device operation requires linear  $V_{CC}$  ramp from  $V_{DR}$  to  $V_{CC}(\text{min}) \geq 100 \mu\text{s}$  or stable at  $V_{CC}(\text{min}) \geq 100 \mu\text{s}$ .

## AC Switching Characteristics

Over the operating range of  $-40\text{ }^{\circ}\text{C}$  to  $85\text{ }^{\circ}\text{C}$

Parameter <sup>[17]</sup>	Description	10 ns		15 ns		Unit
		Min	Max	Min	Max	
<b>Read Cycle</b>						
$t_{\text{POWER}}$	$V_{\text{CC}}$ (stable) to the first access <sup>[18, 19]</sup>	100.0	–	100.0	–	$\mu\text{s}$
$t_{\text{RC}}$	Read cycle time	10.0	–	15.0	–	ns
$t_{\text{AA}}$	Address to data / ERR valid	–	10.0	–	15.0	ns
$t_{\text{OHA}}$	Data / ERR hold from address change	3.0	–	3.0	–	ns
$t_{\text{ACE}}$	$\overline{\text{CE}}$ LOW to data / ERR valid <sup>[20]</sup>	–	10.0	–	15.0	ns
$t_{\text{DOE}}$	$\overline{\text{OE}}$ LOW to data / ERR valid	–	5.0	–	8.0	ns
$t_{\text{LZOE}}$	$\overline{\text{OE}}$ LOW to low Z <sup>[21, 22, 23]</sup>	0	–	1.0	–	ns
$t_{\text{HZOE}}$	$\overline{\text{OE}}$ HIGH to high Z <sup>[21, 22, 23]</sup>	–	5.0	–	8.0	ns
$t_{\text{LZCE}}$	$\overline{\text{CE}}$ LOW to low Z <sup>[20, 21, 22, 23]</sup>	3.0	–	3.0	–	ns
$t_{\text{HZCE}}$	$\overline{\text{CE}}$ HIGH to high Z <sup>[20, 21, 22, 23]</sup>	–	5.0	–	8.0	ns
$t_{\text{PU}}$	$\overline{\text{CE}}$ LOW to power-up <sup>[19, 20]</sup>	0	–	0	–	ns
$t_{\text{PD}}$	$\overline{\text{CE}}$ HIGH to power-down <sup>[19, 20]</sup>	–	10.0	–	15.0	ns
$t_{\text{DBE}}$	Byte enable to data valid	–	5.0	–	8.0	ns
$t_{\text{LZBE}}$	Byte enable to low Z <sup>[21, 22]</sup>	0	–	1.0	–	ns
$t_{\text{HZBE}}$	Byte disable to high Z <sup>[21, 22]</sup>	–	6.0	–	8.0	ns
<b>Write Cycle</b> <sup>[24, 25]</sup>						
$t_{\text{WC}}$	Write cycle time	10.0	–	15.0	–	ns
$t_{\text{SCE}}$	$\overline{\text{CE}}$ LOW to write end <sup>[20]</sup>	7.0	–	12.0	–	ns
$t_{\text{AW}}$	Address setup to write end	7.0	–	12.0	–	ns
$t_{\text{HA}}$	Address hold from write end	0	–	0	–	ns
$t_{\text{SA}}$	Address setup to write start	0	–	0	–	ns
$t_{\text{PWE}}$	$\overline{\text{WE}}$ pulse width	7.0	–	12.0	–	ns
$t_{\text{SD}}$	Data setup to write end	5.0	–	8.0	–	ns
$t_{\text{HD}}$	Data hold from write end	0	–	0	–	ns
$t_{\text{LZWE}}$	$\overline{\text{WE}}$ HIGH to low Z <sup>[21, 22, 23]</sup>	3.0	–	3.0	–	ns
$t_{\text{HZWE}}$	$\overline{\text{WE}}$ LOW to high Z <sup>[21, 22, 23]</sup>	–	5.0	–	8.0	ns
$t_{\text{BW}}$	Byte Enable to write end	7.0	–	12.0	–	ns

### Notes

17. Test conditions assume signal transition time (rise/fall) of 3 ns or less, timing reference levels of 1.5 V (for  $V_{\text{CC}} \geq 3\text{ V}$ ) and  $V_{\text{CC}}/2$  (for  $V_{\text{CC}} < 3\text{ V}$ ), and input pulse levels of 0 to 3 V (for  $V_{\text{CC}} \geq 3\text{ V}$ ) and 0 to  $V_{\text{CC}}$  (for  $V_{\text{CC}} < 3\text{ V}$ ). Test conditions for the read cycle use the output loading, shown in part (a) of [Figure 11 on page 8](#), unless specified otherwise.
18.  $t_{\text{POWER}}$  gives the minimum amount of time that the power supply is at stable  $V_{\text{CC}}$  until the first memory access is performed.
19. These parameters are guaranteed by design and are not tested.
20. For all dual chip enable devices,  $\overline{\text{CE}}$  is the logical combination of  $\overline{\text{CE}}_1$  and  $\text{CE}_2$ . When  $\overline{\text{CE}}_1$  is LOW and  $\text{CE}_2$  is HIGH,  $\overline{\text{CE}}$  is LOW; when  $\overline{\text{CE}}_1$  is HIGH or  $\text{CE}_2$  is LOW,  $\overline{\text{CE}}$  is HIGH.
21.  $t_{\text{HZOE}}$ ,  $t_{\text{HZCE}}$ ,  $t_{\text{HZWE}}$ , and  $t_{\text{HZBE}}$  are specified with a load capacitance of 5 pF, as shown in part (b) of [Figure 11 on page 8](#). Hi-Z, Lo-Z transition is measured  $\pm 200\text{ mV}$  from steady state voltage.
22. At any temperature and voltage condition,  $t_{\text{HZCE}}$  is less than  $t_{\text{LZCE}}$ ,  $t_{\text{HZBE}}$  is less than  $t_{\text{LZBE}}$ ,  $t_{\text{HZOE}}$  is less than  $t_{\text{LZOE}}$ , and  $t_{\text{HZWE}}$  is less than  $t_{\text{LZWE}}$  for any device.
23. Tested initially and after any design or process changes that may affect these parameters.
24. The internal write time of the memory is defined by the overlap of  $\overline{\text{WE}} = V_{\text{IL}}$ ,  $\overline{\text{CE}} = V_{\text{IL}}$ , and  $\overline{\text{BHE}}$  or  $\overline{\text{BLE}} = V_{\text{IL}}$ . These signals must be LOW to initiate a write, and the HIGH transition of any of these signals can terminate the operation. The input data setup and hold timing should be referenced to the edge of the signal that terminates the write.
25. The minimum write pulse width for Write Cycle No. 2 ( $\overline{\text{WE}}$  controlled,  $\overline{\text{OE}}$  LOW) should be sum of  $t_{\text{HZWE}}$  and  $t_{\text{SD}}$ .

Switching Waveforms

Figure 13. Read Cycle No. 1 of CY7C1061G (Address Transition Controlled) [26, 27]

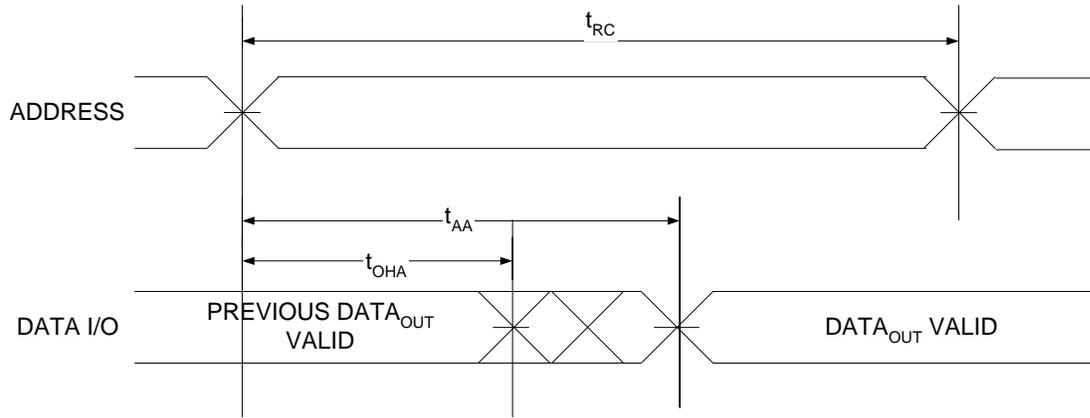
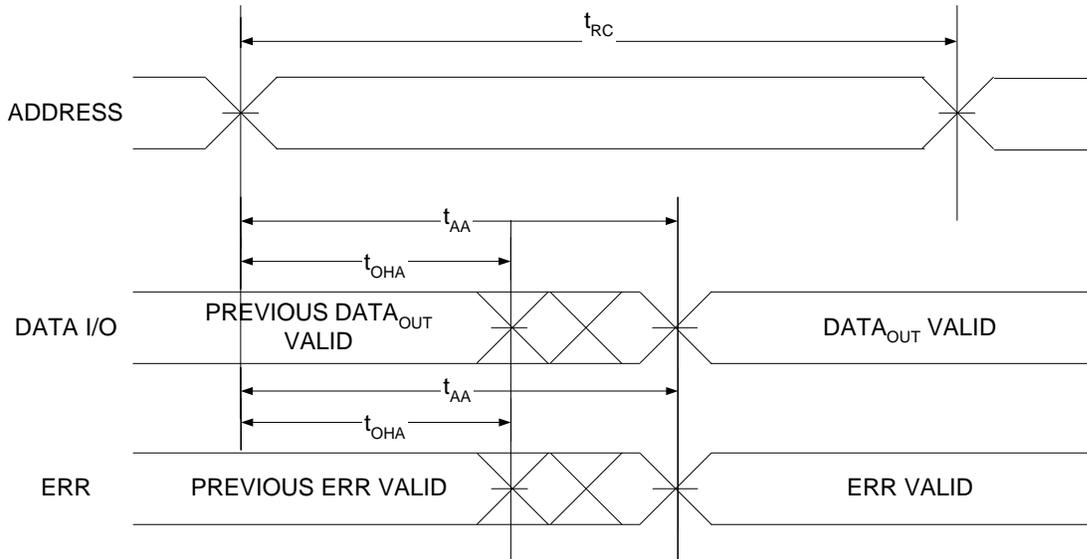


Figure 14. Read Cycle No. 2 of CY7C1061GE (Address Transition Controlled) [26, 27]

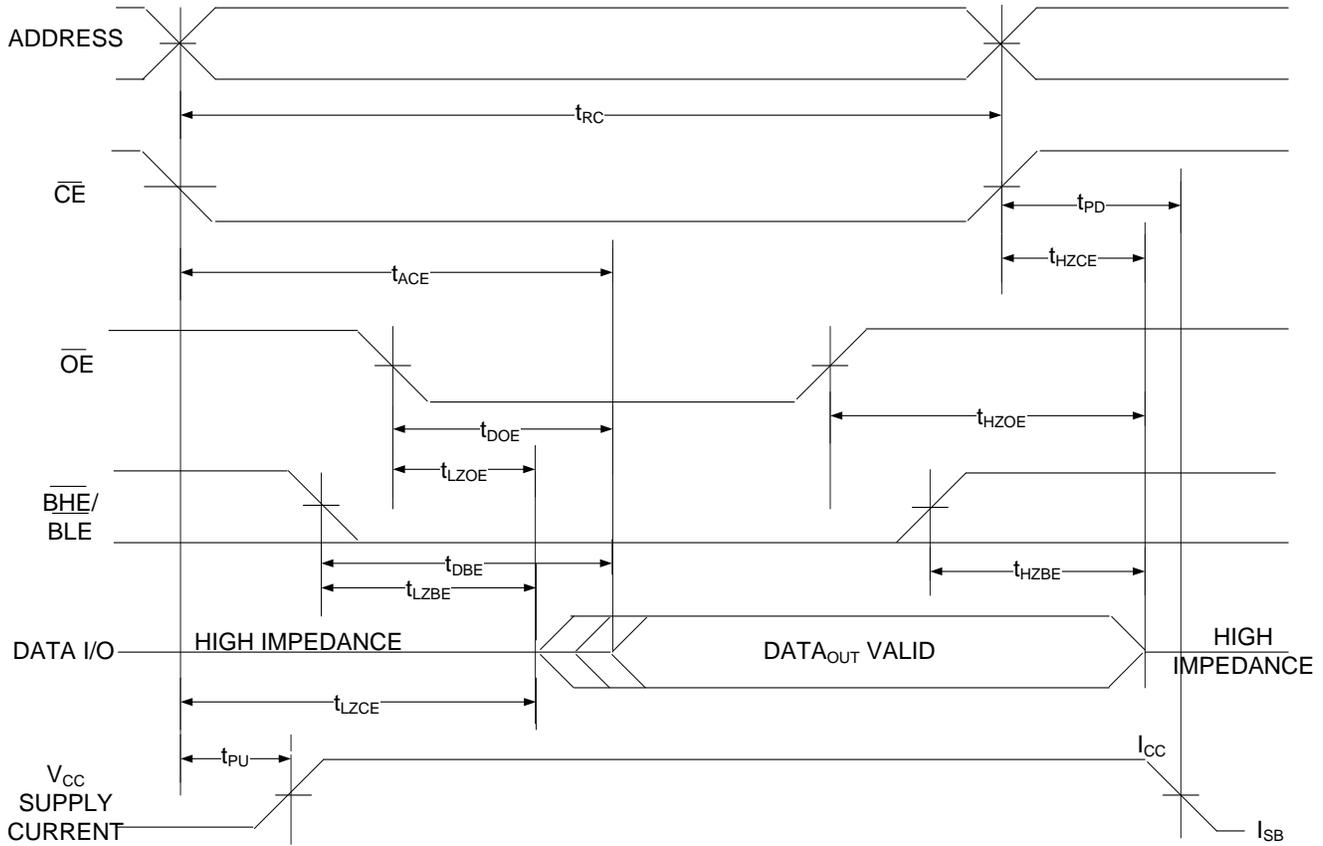


Notes

- 26. The device is continuously selected,  $\overline{OE} = V_{IL}$ ,  $\overline{CE} = V_{IL}$ ,  $\overline{BHE}$  or  $\overline{BLE}$  or both =  $V_{IL}$ .
- 27.  $\overline{WE}$  is HIGH for read cycle.

Switching Waveforms (continued)

Figure 15. Read Cycle No. 3 ( $\overline{OE}$  Controlled) [28, 29, 30]



Notes

- 28. For all dual chip enable devices,  $\overline{CE}$  is the logical combination of  $\overline{CE}_1$  and  $CE_2$ . When  $\overline{CE}_1$  is LOW and  $CE_2$  is HIGH,  $\overline{CE}$  is LOW; when  $\overline{CE}_1$  is HIGH or  $CE_2$  is LOW,  $\overline{CE}$  is HIGH.
- 29.  $\overline{WE}$  is HIGH for read cycle.
- 30. Address valid prior to or coincident with  $\overline{CE}$  LOW transition.

Switching Waveforms (continued)

Figure 16. Write Cycle No. 1 ( $\overline{CE}$  Controlled) [31, 32, 33]

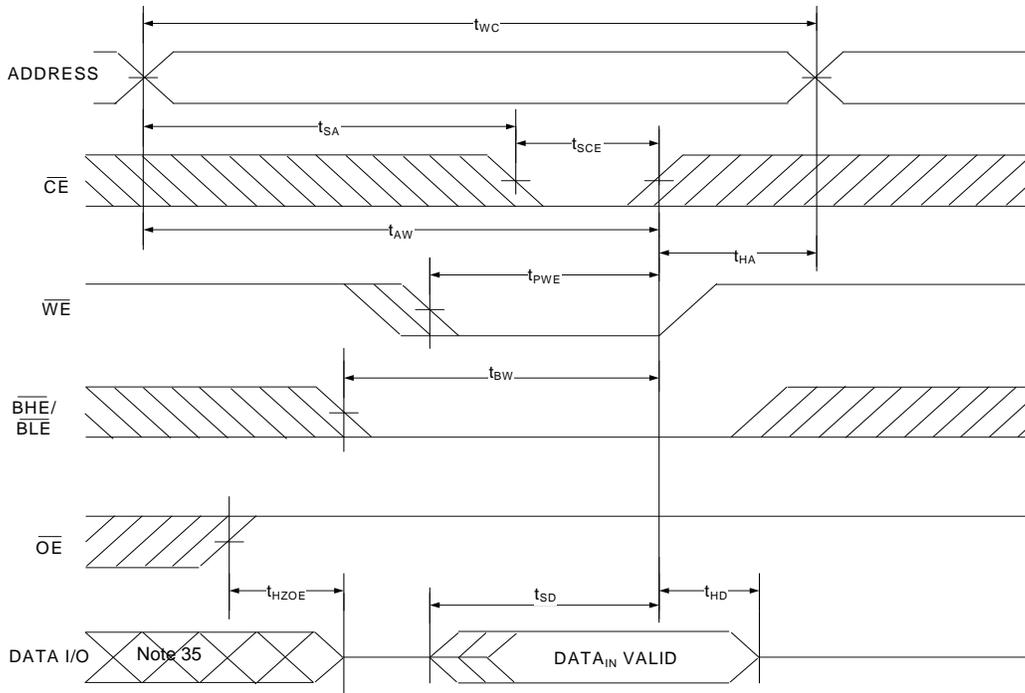
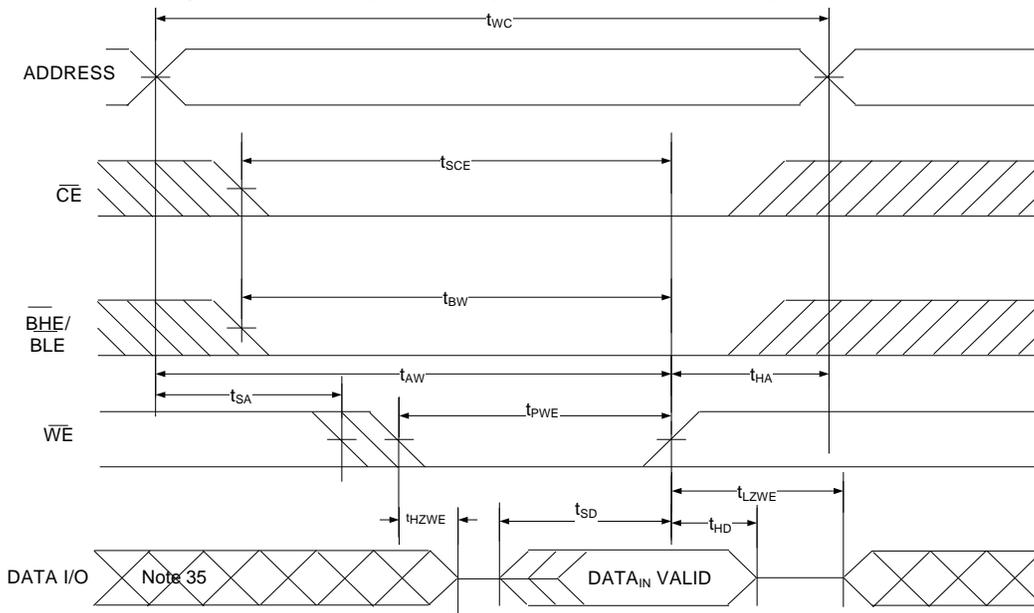


Figure 17. Write Cycle No. 2 ( $\overline{WE}$  Controlled,  $\overline{OE}$  LOW) [31, 32, 33, 34]

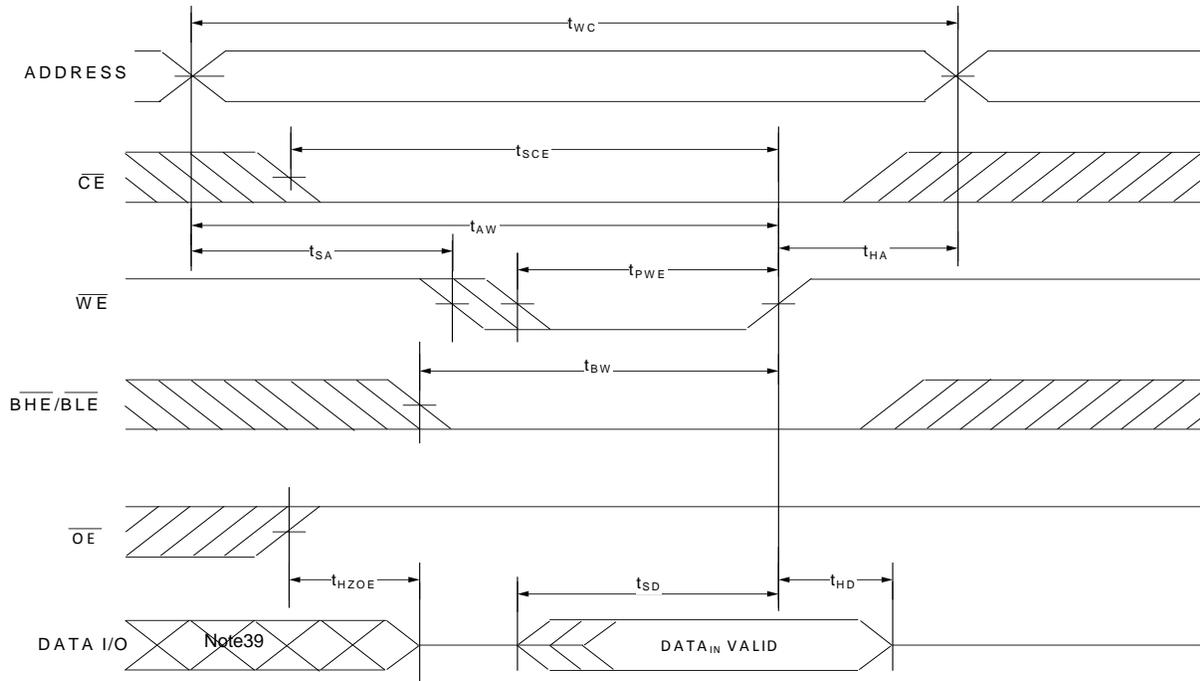


Notes

- 31. For all dual chip enable devices,  $\overline{CE}$  is the logical combination of  $\overline{CE}_1$  and  $CE_2$ . When  $\overline{CE}_1$  is LOW and  $CE_2$  is HIGH,  $\overline{CE}$  is LOW; when  $\overline{CE}_1$  is HIGH or  $CE_2$  is LOW,  $\overline{CE}$  is HIGH.
- 32. The internal write time of the memory is defined by the overlap of  $\overline{WE} = V_{IL}$ ,  $\overline{CE} = V_{IL}$  and  $\overline{BHE}$  or  $\overline{BLE} = V_{IL}$ . These signals must be LOW to initiate a write, and the HIGH transition of any of these signals can terminate the operation. The input data setup and hold timing should be referenced to the edge of the signal that terminates the write.
- 33. Data I/O is in high-impedance state if  $\overline{CE} = V_{IH}$ , or  $\overline{OE} = V_{IH}$  or  $\overline{BHE}$ , and/or  $\overline{BLE} = V_{IH}$ .
- 34. The minimum write cycle pulse width should be equal to sum of  $t_{HZWE}$  and  $t_{SD}$ .
- 35. During this period the I/Os are in output state. Do not apply input signals.

Switching Waveforms (continued)

Figure 18. Write Cycle No. 3 ( $\overline{WE}$  controlled)<sup>[36, 37, 38]</sup>

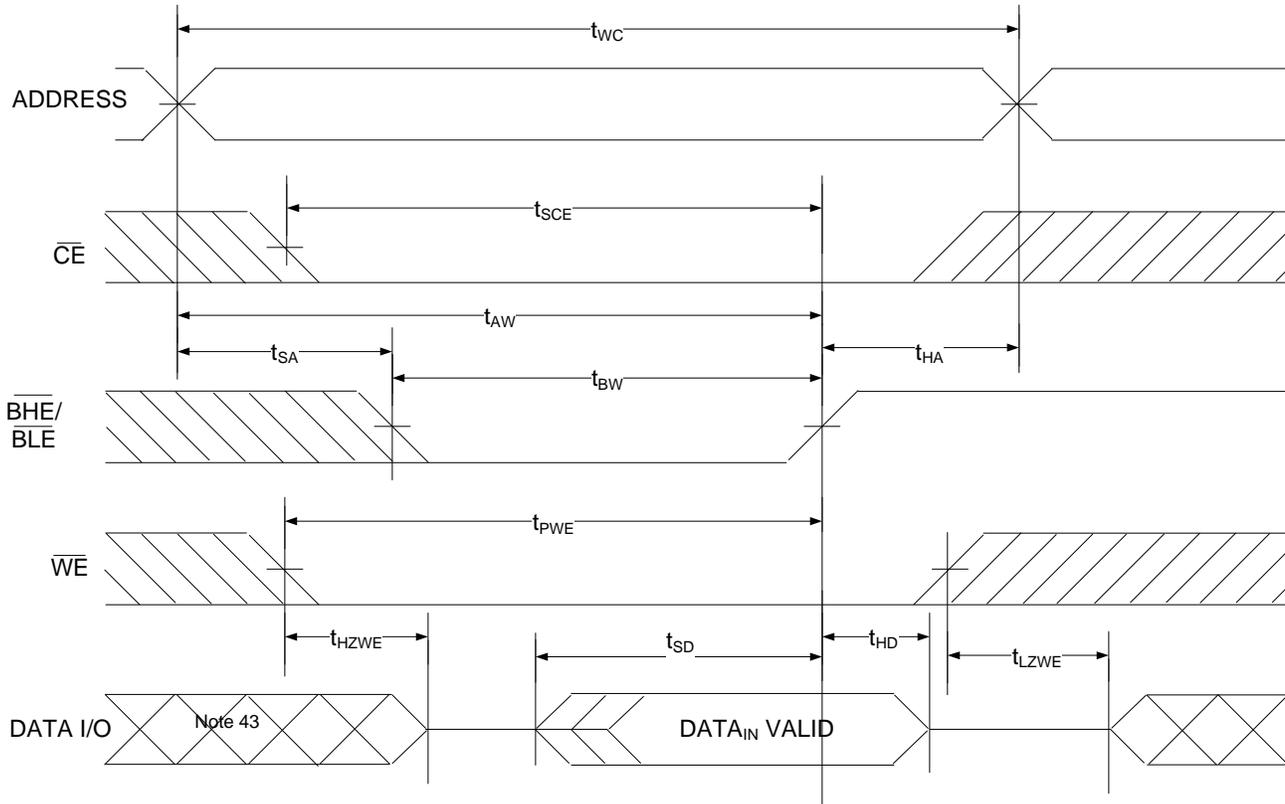


Notes

- 36. For all dual chip enable devices,  $\overline{CE}$  is the logical combination of  $\overline{CE}_1$  and  $CE_2$ . When  $\overline{CE}_1$  is LOW and  $CE_2$  is HIGH,  $\overline{CE}$  is LOW; when  $\overline{CE}_1$  is HIGH or  $CE_2$  is LOW,  $\overline{CE}$  is HIGH.
- 37. The internal write time of the memory is defined by the overlap of  $\overline{WE} = V_{IL}$ ,  $\overline{CE} = V_{IL}$  and  $\overline{BHE}$  or  $\overline{BLE} = V_{IL}$ . These signals must be LOW to initiate a write, and the HIGH transition of any of these signals can terminate the operation. The input data setup and hold timing should be referenced to the edge of the signal that terminates the write.
- 38. Data I/O is in high-impedance state if  $\overline{CE} = V_{IH}$ , or  $\overline{OE} = V_{IH}$  or  $\overline{BHE}$ , and/or  $\overline{BLE} = V_{IH}$ .
- 39. During this period, the I/Os are in output state. Do not apply input signals.

Switching Waveforms (continued)

Figure 19. Write Cycle No. 4 (BLE or BHE Controlled) [40, 41, 42]



Notes

- 40. For all dual chip enable devices,  $\overline{CE}$  is the logical combination of  $\overline{CE}_1$  and  $CE_2$ . When  $\overline{CE}_1$  is LOW and  $CE_2$  is HIGH,  $\overline{CE}$  is LOW; when  $\overline{CE}_1$  is HIGH or  $CE_2$  is LOW,  $\overline{CE}$  is HIGH.
- 41. The internal write time of the memory is defined by the overlap of  $\overline{WE} = V_{IL}$ ,  $\overline{CE} = V_{IL}$  and  $\overline{BHE}$  or  $\overline{BLE} = V_{IL}$ . These signals must be LOW to initiate a write, and the HIGH transition of any of these signals can terminate the operation. The input data setup and hold timing should be referenced to the edge of the signal that terminates the write.
- 42. Data I/O is in high-impedance state if  $\overline{CE} = V_{IH}$ , or  $\overline{OE} = V_{IH}$  or  $\overline{BHE}$ , and/or  $\overline{BLE} = V_{IH}$ .
- 43. During this period, the I/Os are in output state. Do not apply input signals.

**Truth Table**

$\overline{CE}$ [44]	$\overline{OE}$	$\overline{WE}$	$\overline{BLE}$	$\overline{BHE}$	I/O <sub>0</sub> -I/O <sub>7</sub>	I/O <sub>8</sub> -I/O <sub>15</sub>	Mode	Power
H	X <sup>[45]</sup>	X <sup>[45]</sup>	X <sup>[45]</sup>	X <sup>[45]</sup>	High-Z	High-Z	Power down	Standby (I <sub>SB</sub> )
L	L	H	L	L	Data out	Data out	Read all bits	Active (I <sub>CC</sub> )
L	L	H	L	H	Data out	High-Z	Read lower bits only	Active (I <sub>CC</sub> )
L	L	H	H	L	High-Z	Data out	Read upper bits only	Active (I <sub>CC</sub> )
L	X	L	L	L	Data in	Data in	Write all bits	Active (I <sub>CC</sub> )
L	X	L	L	H	Data in	High-Z	Write lower bits only	Active (I <sub>CC</sub> )
L	X	L	H	L	High-Z	Data in	Write upper bits only	Active (I <sub>CC</sub> )
L	H	H	X	X	High-Z	High-Z	Selected, outputs disabled	Active (I <sub>CC</sub> )
L	X	X	H	H	High-Z	High-Z	Selected, outputs disabled	Active (I <sub>CC</sub> )

**ERR Output – CY7C1061GE**

Output [46]	Mode
0	Read operation, no single-bit error in the stored data.
1	Read operation, single-bit error detected and corrected.
High-Z	Device deselected or outputs disabled or Write operation

**Notes**

44. For all dual chip enable devices,  $\overline{CE}$  is the logical combination of  $\overline{CE}_1$  and  $CE_2$ . When  $\overline{CE}_1$  is LOW and  $CE_2$  is HIGH,  $\overline{CE}$  is LOW; when  $\overline{CE}_1$  is HIGH or  $CE_2$  is LOW,  $\overline{CE}$  is HIGH.

45. The input voltage levels on these pins should be either at  $V_{IH}$  or  $V_{IL}$ .

46. ERR is an Output pin. If not used, this pin should be left floating.

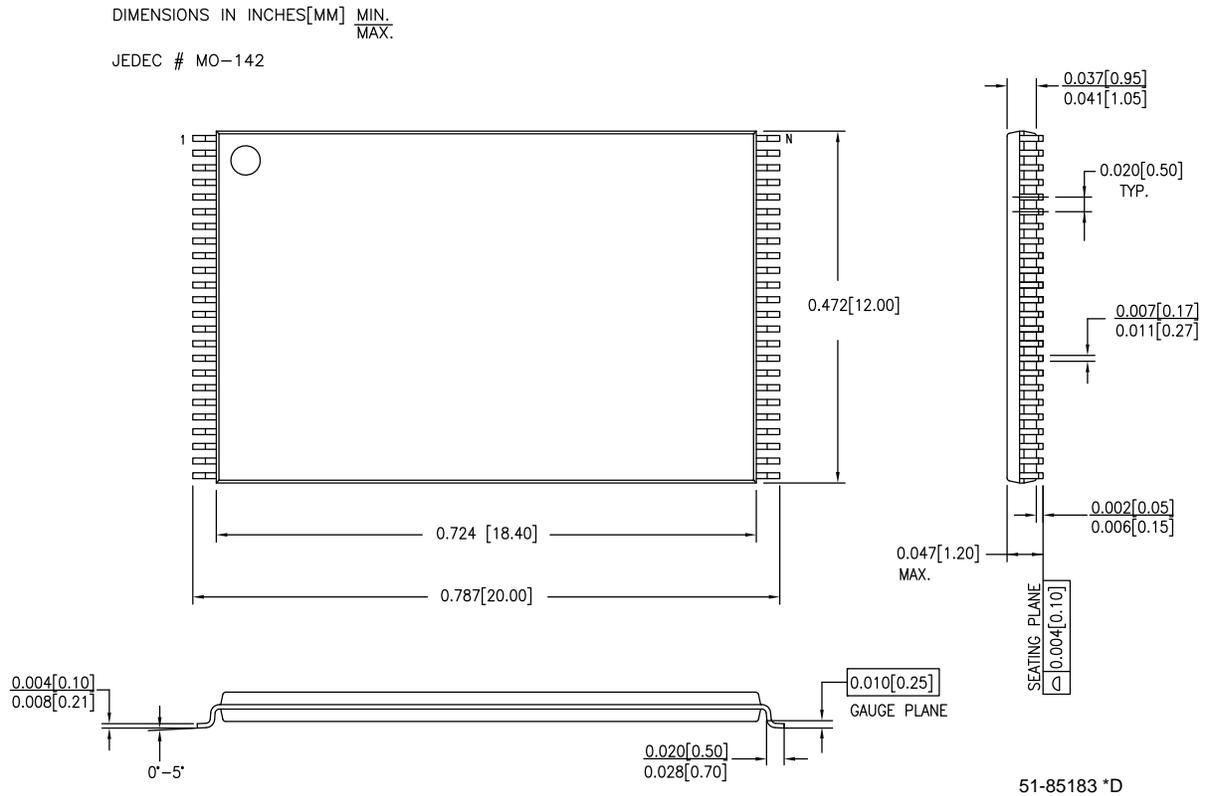
**Ordering Information**

Speed (ns)	Voltage Range	Ordering Code	Package Diagram	Package Type (all Pb-free)	Key Features/Differentiators	ERR Pin/Ball	Operating Range				
10	4.5 V–5.5 V	CY7C1061G-10BV1XI	51-85150	48-ball VFBGA	Single Chip Enable	No					
		CY7C1061GE-10BV1XI			Address MSB A19 at ball G2	Yes					
		CY7C1061G-10BVJXI			Dual Chip Enable	No					
		CY7C1061GE-10BVJXI			Address MSB A19 at ball G2	Yes					
		CY7C1061G-10BVXI			Dual Chip Enable	No					
		CY7C1061GE-10BVXI			Address MSB A19 at ball H6	Yes					
	2.2 V–3.6 V	51-85160	54-pin TSOP II	CY7C1061G-10ZSXI	Dual Chip Enable	No					
				CY7C1061GE-10ZSXI		Yes					
				51-85183	48-pin TSOP I	CY7C1061G-10ZXI	Single Chip Enable	No			
						CY7C1061GE-10ZXI		Yes			
						51-85150	48-ball VFBGA	CY7C1061G30-10BV1XI	Single Chip Enable	No	
								CY7C1061GE30-10BV1XI	Address MSB A19 at ball G2	Yes	
	CY7C1061G30-10BVJXI	Dual Chip Enable	No								
	CY7C1061GE30-10BVJXI	Address MSB A19 at ball G2	Yes								
	CY7C1061G30-10BVXI	Dual Chip Enable	No	Industrial							
	CY7C1061GE30-10BVXI	Address MSB A19 at ball H6	Yes								
	1.65 V–2.2 V	51-85160	54-pin TSOP II	CY7C1061G30-10ZSXI	Dual Chip Enable	No					
				CY7C1061GE30-10ZSXI		Yes					
51-85183				48-pin TSOP I	CY7C1061G30-10ZXI	Single Chip Enable	No				
					CY7C1061GE30-10ZXI		Yes				
					51-85150	48-ball VFBGA	CY7C1061GE18-15BV1XI	Single Chip Enable	Yes		
							CY7C1061G18-15BV1XI	Address MSB A19 at ball G2	No		
CY7C1061GE18-15BVJXI	Dual Chip Enable	Yes									
CY7C1061G18-15BVJXI	Address MSB A19 at ball G2	No									
CY7C1061GE18-15BVXI	Dual Chip Enable	Yes									
CY7C1061G18-15BVXI	Address MSB A19 at ball H6	No									
51-85160	54-pin TSOP II	CY7C1061GE18-15ZSXI	Dual Chip Enable	Yes							
		CY7C1061G18-15ZSXI		No							
		51-85183	48-pin TSOP I	CY7C1061GE18-15ZXI	Single Chip Enable	Yes					
				CY7C1061G18-15ZXI		No					



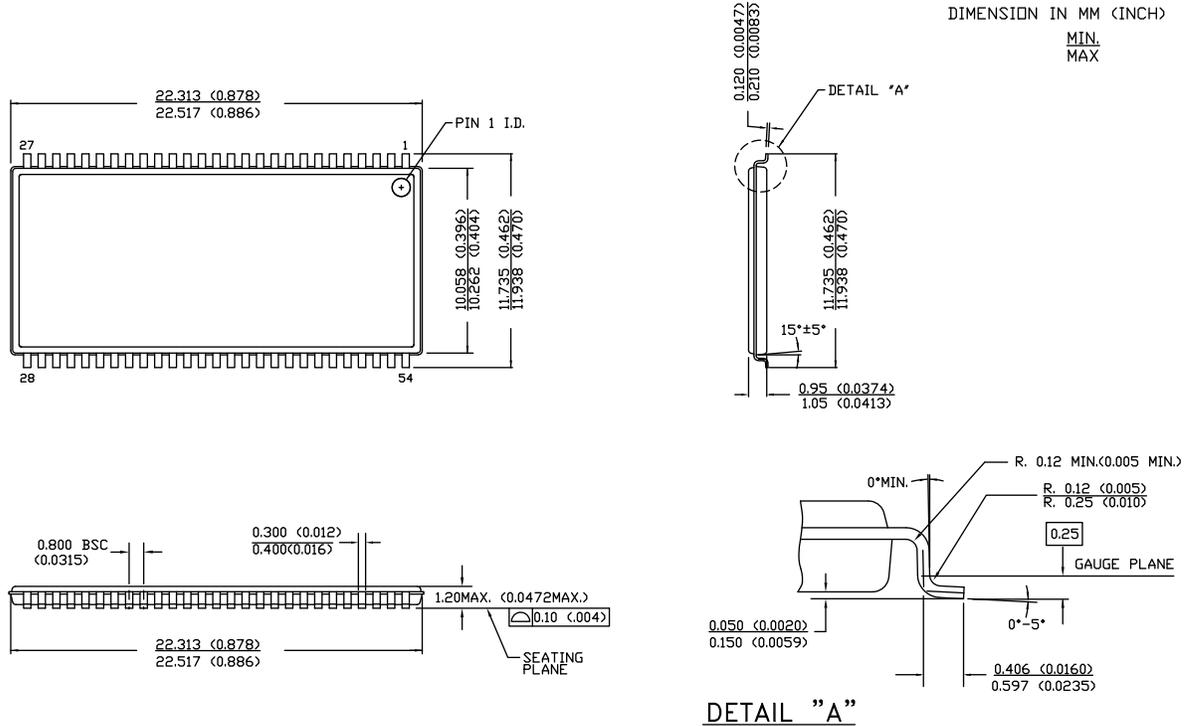
Package Diagrams

Figure 20. 48-pin TSOP I (12 × 18.4 × 1.0 mm) Z48A Package Outline



Package Diagrams (continued)

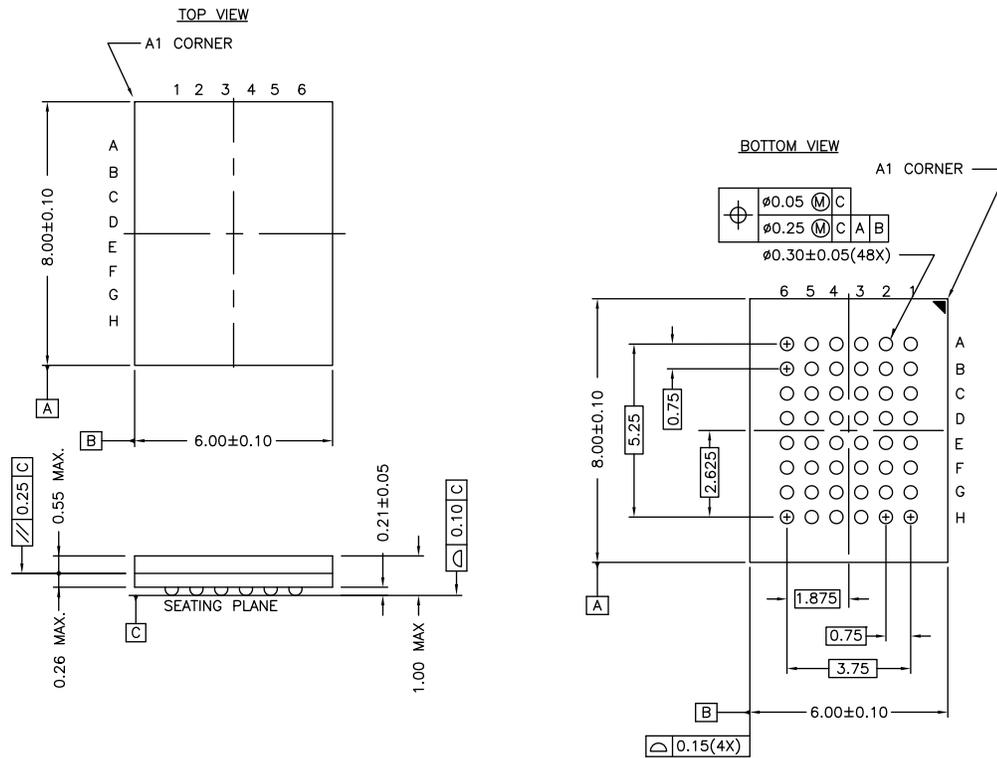
Figure 21. 54-pin TSOP II (22.4 x 11.84 x 1.0 mm) Z54-II Package Outline



51-85160 \*E

Package Diagrams (continued)

Figure 22. 48-ball VFBGA (6 × 8 × 1.0 mm) BV48/BZ48 Package Outline



NOTE:  
 PACKAGE WEIGHT: See Cypress Package Material Declaration Datasheet (PMDD) posted on the Cypress web.

51-85150 \*H

## Acronyms

Acronym	Description
$\overline{\text{BHE}}$	Byte High Enable
$\overline{\text{BLE}}$	Byte Low Enable
$\overline{\text{CE}}$	Chip Enable
CMOS	Complementary metal oxide semiconductor
I/O	Input/output
$\overline{\text{OE}}$	Output Enable
SRAM	Static random access memory
TSOP	Thin small outline package
TTL	Transistor-transistor logic
VFBGA	Very fine-pitch ball grid array
$\overline{\text{WE}}$	Write Enable

## Document Conventions

### Units of Measure

Symbol	Unit of Measure
°C	degree Celsius
MHz	megahertz
μA	microampere
μs	microsecond
mA	milliampere
mm	millimeter
ns	nanosecond
Ω	ohm
%	percent
pF	picofarad
V	volt
W	watt

## Document History Page

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Document Number: 001-81540

Rev.	ECN No.	Orig. of Change	Submission Date	Description of Change
*P	4791835	NILE	06/09/2015	Changed datasheet status to Final

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